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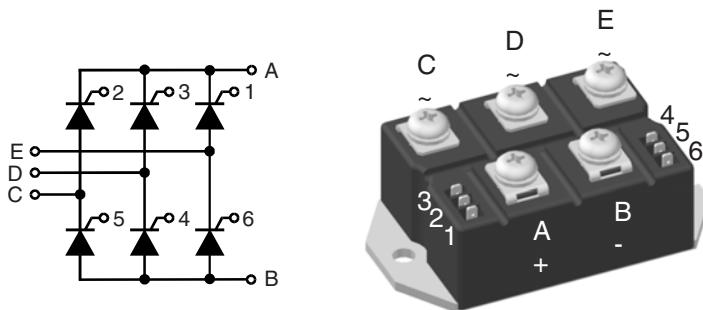
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Three Phase Full Controlled Rectifier Bridge, B6C

$I_{dAVM} = 110/167 \text{ A}$
 $V_{RRM} = 1200-1600 \text{ V}$

Preliminary data

V_{RSM} V_{DSM}	V_{RRM} V_{DRM}	Type
V	V	
1300	1200	VTO 110-12io7
1500	1400	VTO 110-14io7
1700	1600	VTO 175-16io7



Symbol	Test Conditions	Maximum Ratings	
		VTO 110	VTO 175
I_{dAV}	$T_c = 85^\circ\text{C}$; module per leg	110 58	167 89
I_{FRMS}, I_{TRMS}	$T_{vJ} = 45^\circ\text{C}$; $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $T_{vJ} = T_{vJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$	1150 1230 1000 1070	1500 1600 1350 1450
I^2t	$T_{vJ} = 45^\circ\text{C}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine $T_{vJ} = T_{vJM}$ $t = 10 \text{ ms}$ (50 Hz), sine $V_R = 0$ $t = 8.3 \text{ ms}$ (60 Hz), sine	6600 6280 5000 4750	11200 10750 9100 8830
$(di/dt)_cr$	$T_{vJ} = T_{vJM}$ repetitive, $I_T = 50 \text{ A}$ $f = 400 \text{ Hz}$, $t_p = 200 \mu\text{s}$ $V_D = 2/3 V_{DRM}$ $I_G = 0.3 \text{ A}$, non repetitive $di_G/dt = 0.3 \text{ A}/\mu\text{s}$, $I_T = 1/3 \cdot I_{dAV}$	150	A/ μs
$(dv/dt)_cr$	$T_{vJ} = T_{vJM}$; $V_{DR} = 2/3 V_{DRM}$ $R_{GK} = \infty$; method 1 (linear voltage rise)	1000	V/ μs
V_{RGM}		10	V
P_{GM}	$T_{vJ} = T_{vJM}$ $t_p = 30 \mu\text{s}$ $I_T = I_{TAVM}$ $t_p = 500 \mu\text{s}$ $t_p = 10 \text{ ms}$	\leq \leq \leq 0.5	W W W W
P_{GAVM}		-40...+125 125 -40...+125	°C °C °C
T_{vJ}			
T_{vJM}			
T_{stg}			
V_{ISOL}	50/60 Hz, RMS $t = 1 \text{ min}$ $I_{ISOL} \leq 1 \text{ mA}$ $t = 1 \text{ s}$	2500 3000	V~ V~
M_d	Mounting torque (M6) Terminal connection torque (M6)	5-15 5-15 300	Nm lb.in. g
Weight	typ.		

Data according to IEC 60747 and refer to a single thyristor/diode unless otherwise stated.

IXYS reserves the right to change limits, test conditions and dimensions.

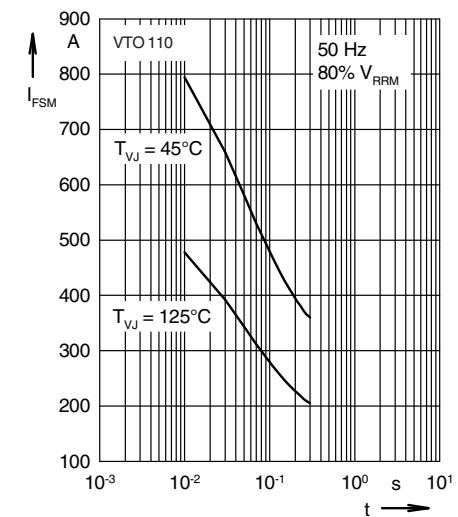
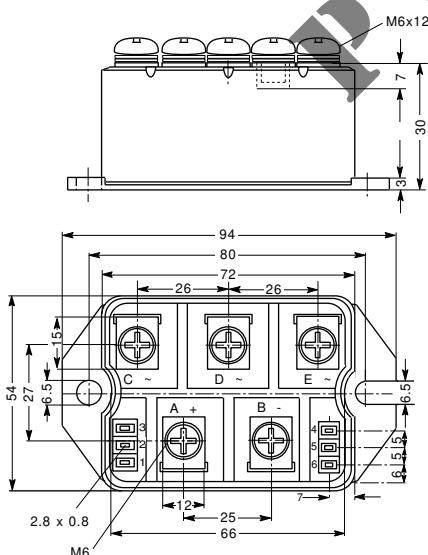
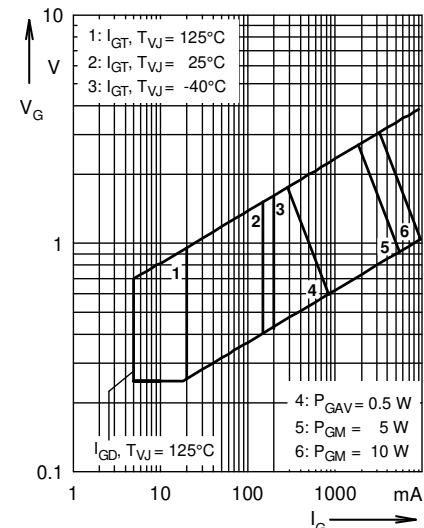
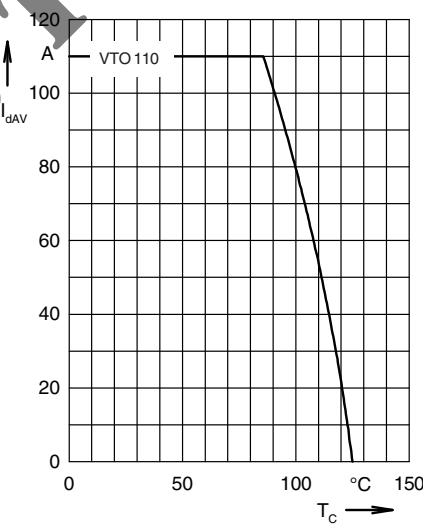
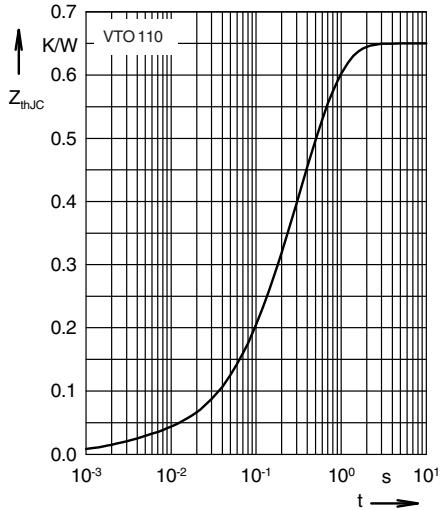
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Symbol **Test Conditions**

		Characteristic Values		
		VTO 110	VTO 175	
I_R, I_D	$V_R = V_{RRM}; V_D = V_{DRM}$ $T_{VJ} = T_{VJM}$ $T_{VJ} = 25^\circ C$	\leq \leq	5 0.3	mA mA
V_F, V_T	$I_F, I_T = 200 A, T_{VJ} = 25^\circ C$	\leq	1.75	1.57 V
V_{TO} r_T	For power-loss calculations only $(T_{VJ} = 125^\circ C)$		0.85 6	0.85 V 3.5 mΩ
V_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	\leq \leq	1.5 1.6	V V
I_{GT}	$V_D = 6 V; T_{VJ} = 25^\circ C$ $T_{VJ} = -40^\circ C$	\leq \leq	100 200	mA mA
V_{GD} I_{GD}	$T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$ $T_{VJ} = T_{VJM}; V_D = \frac{2}{3} V_{DRM}$	\leq \leq	0.2 5	V mA
I_L	$I_G = 0.3 A; t_G = 30 \mu s$ $di_G/dt = 0.3 A/\mu s$	$T_{VJ} = 25^\circ C$	\leq	450 mA
I_H	$T_{VJ} = 25^\circ C; V_D = 6 V; R_{GK} = \infty$	\leq	200	mA
t_{gd}	$T_{VJ} = 25^\circ C; V_D = \frac{1}{2} V_{DRM}$ $I_G = 0.3 A; di_G/dt = 0.3 A/\mu s$	\leq	2	μs
R_{thJC}	per thyristor (diode); DC current	0.65	0.46	K/W
	per module	0.108	0.077	K/W
R_{thJH}	per thyristor (diode); DC current	0.8	0.55	K/W
	per module	0.133	0.092	K/W
d_s d_A a	Creeping distance on surface Creepage distance in air Max. allowable acceleration	10 9.4 50	mm mm m/s ²	

Dimensions in mm (1 mm = 0.0394")

Fig. 3 Surge overload current
 I_{FSM} : Crest value, t : duration

Fig. 1 Gate trigger characteristics

Fig. 2 DC output current at case temperature

Fig. 4 Transient thermal impedance junction to case (per leg)